

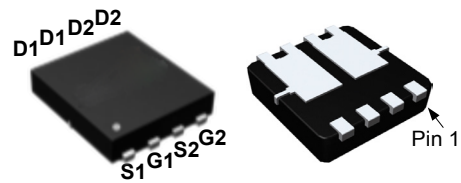
Features

- 30V/-45A
 $R_{DS(ON)} = 12m\Omega (typ.) @ V_{GS} = -10V$
 $R_{DS(ON)} = 22m\Omega (typ.) @ V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

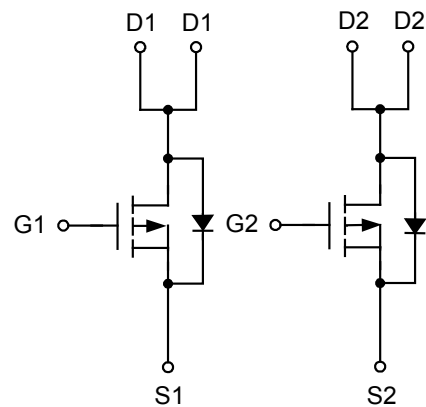
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Pin Description



DFN5x6C-8_EP2



P-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-45	A
I _D	Continuous Drain Current	T _C =25°C	-45	A
		T _C =100°C	-27	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-135	
P _D	Maximum Power Dissipation	T _C =25°C	25	W
		T _C =100°C	10	
R _{θJC}	Thermal Resistance-Junction to Case		5	°C/W
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	Steady state	95	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.1mH	-23	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.1mH	26	mJ

Note * : Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 8A.

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Note c : Surface Mounted on 1in^2 pad area.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

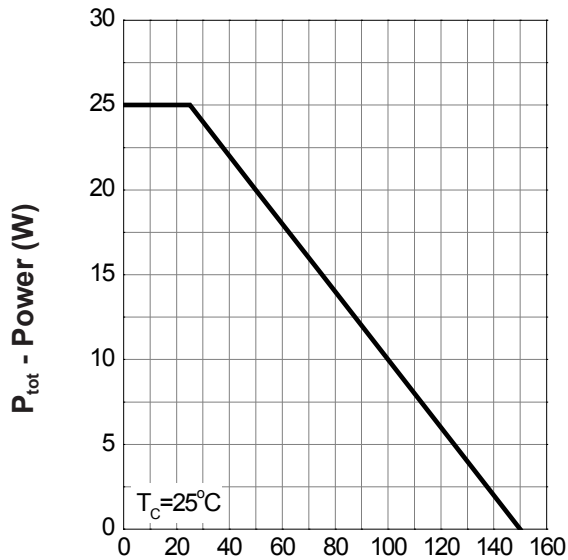
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =85°C	-	-	-1	μA
			-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.5	-2	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-6A V _{GS} =-4.5V, I _{DS} =-4A	-	12	15	mΩ
			-	22	26	
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-4A, V _{GS} =0V	-	-0.8	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-6A, dI _{SD} /dt=100A/μs	-	19	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	7	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz	-	1270	1650	pF
C _{oss}	Output Capacitance		-	255	-	
C _{rss}	Reverse Transfer Capacitance		-	165	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =15Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	11	20	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	81	146	
t _f	Turn-off Fall Time		-	50	90	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-6A	-	13.8	-	nC
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-10V, I _{DS} =-6A	-	28	39	
Q _{gs}	Gate-Source Charge		-	4.6	-	
Q _{gd}	Gate-Drain Charge		-	6.6	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

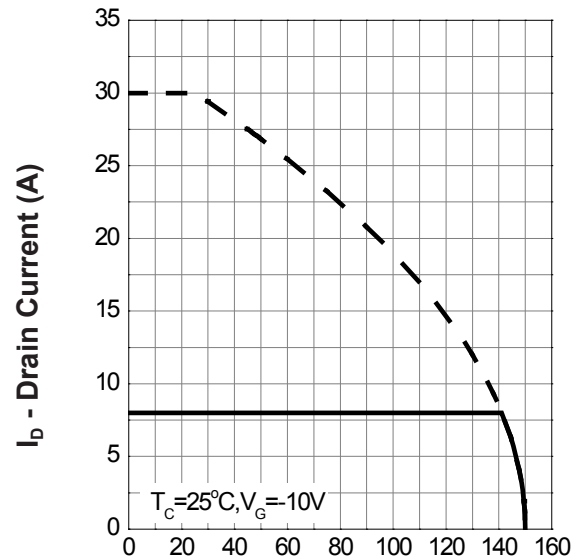
Typical Operating Characteristics

Power Dissipation



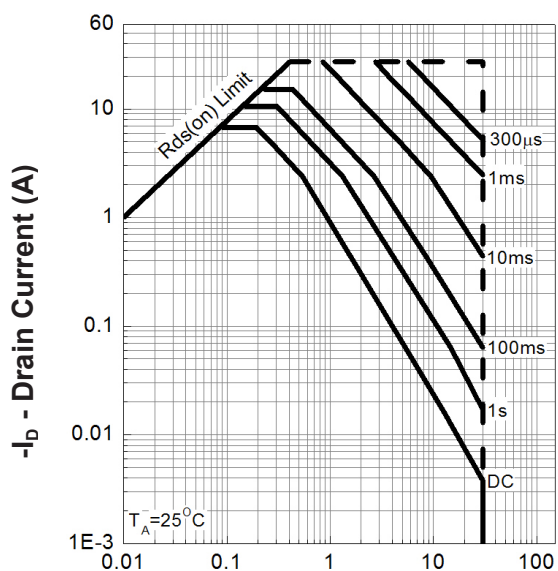
T_j - Junction Temperature ($^{\circ}\text{C}$)

Drain Current



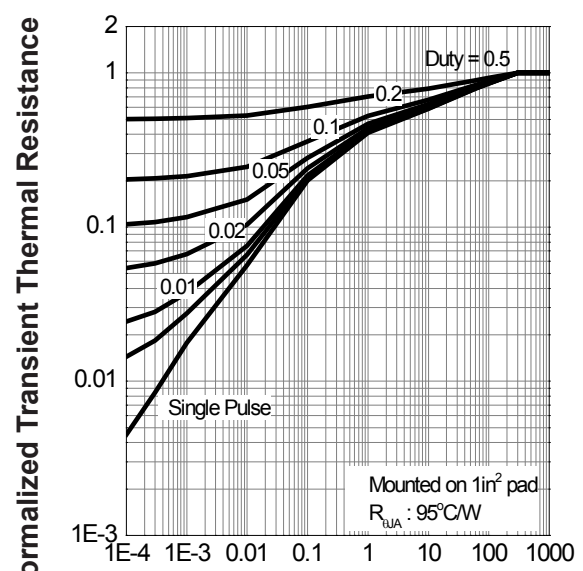
T_j - Junction Temperature ($^{\circ}\text{C}$)

Safe Operation Area



$-V_{DS}$ - Drain - Source Voltage (V)

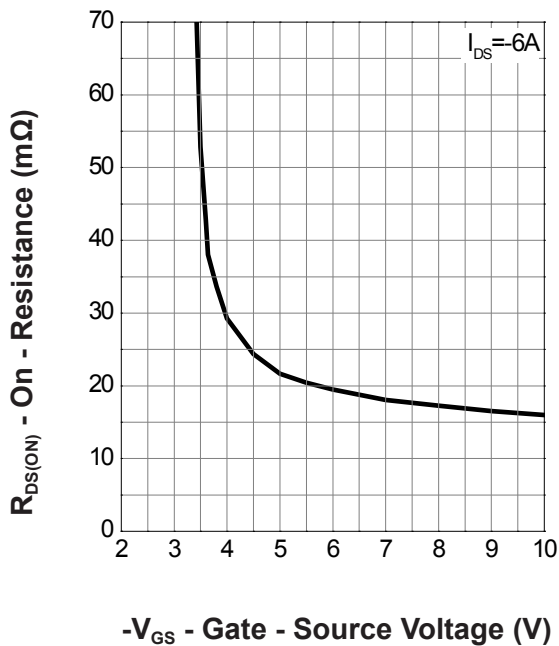
Thermal Transient Impedance



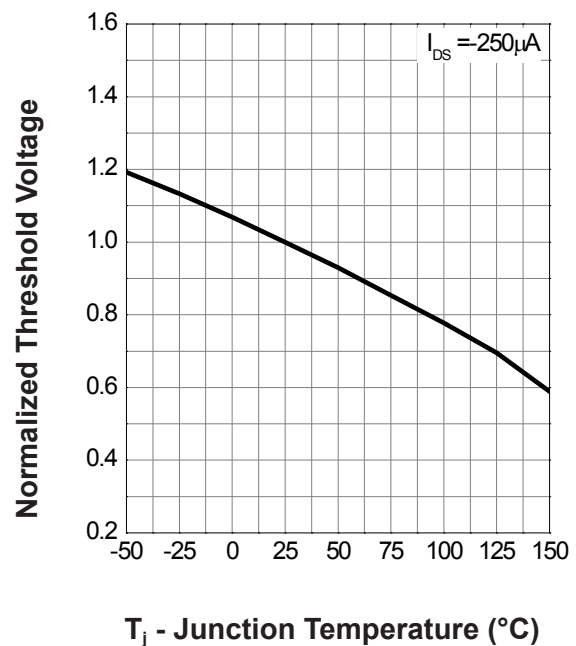
Square Wave Pulse Duration (sec)

Typical Operating Characteristics(Cont.)

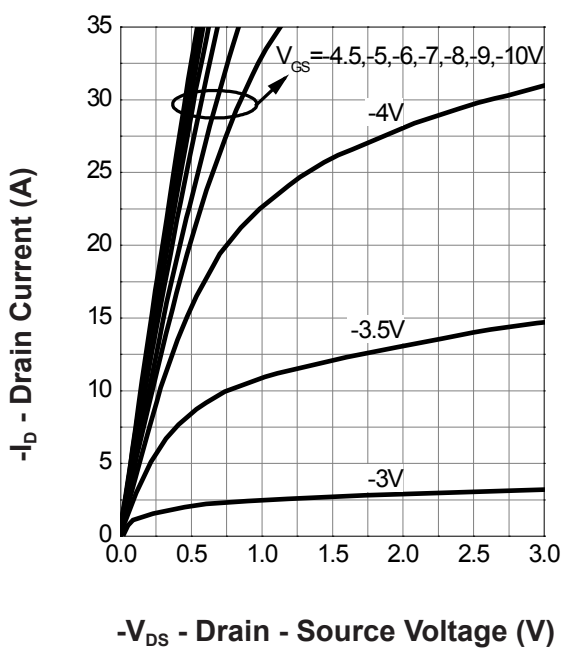
Gate-Source On Resistance



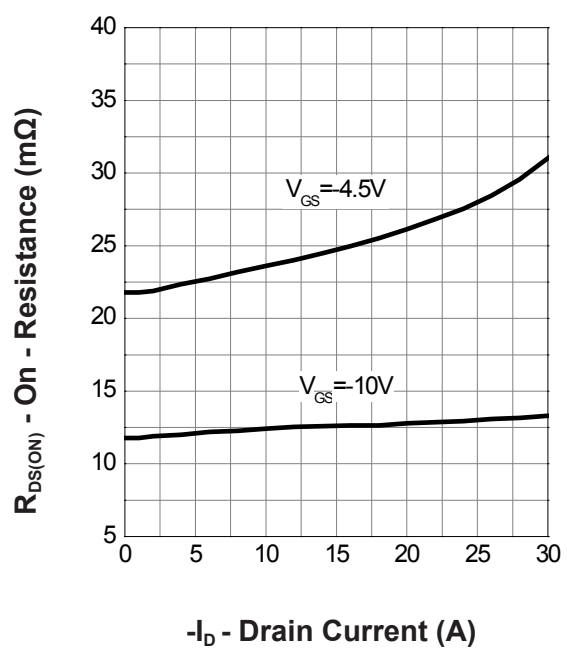
Gate Threshold Voltage



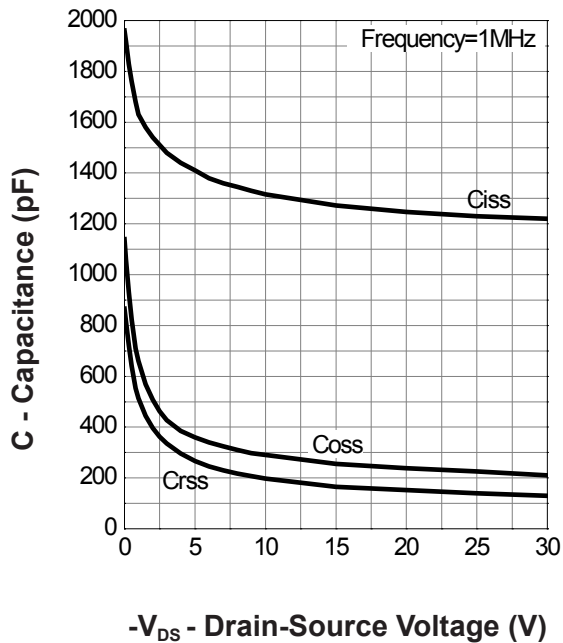
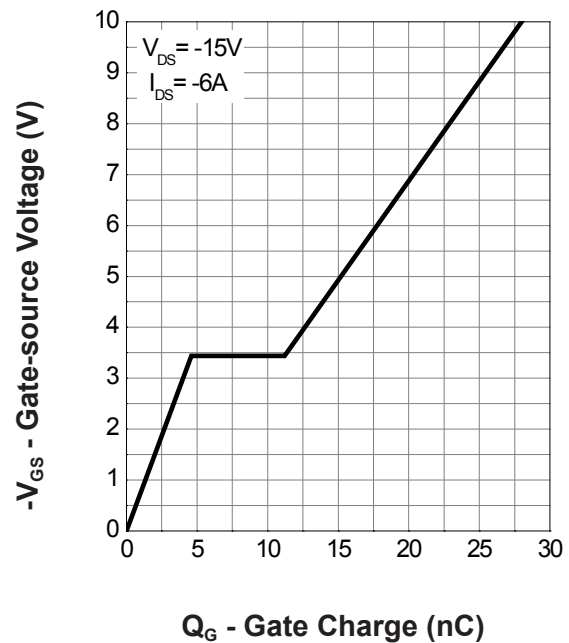
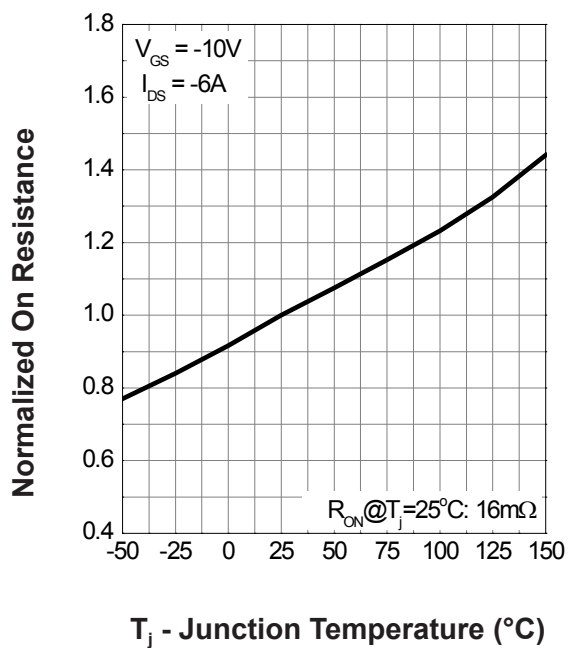
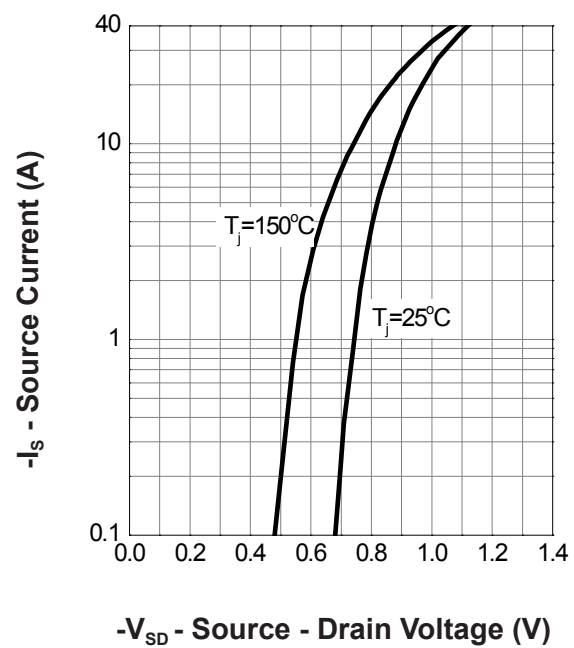
Output Characteristics



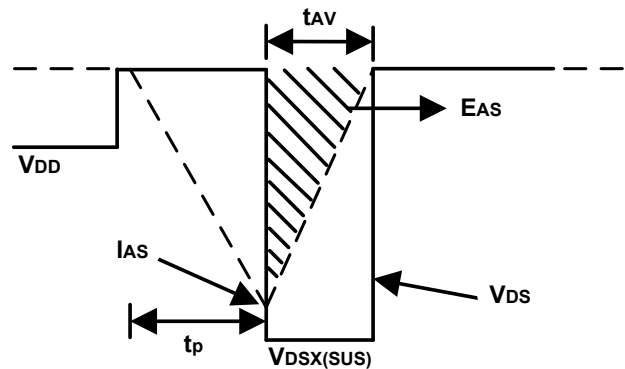
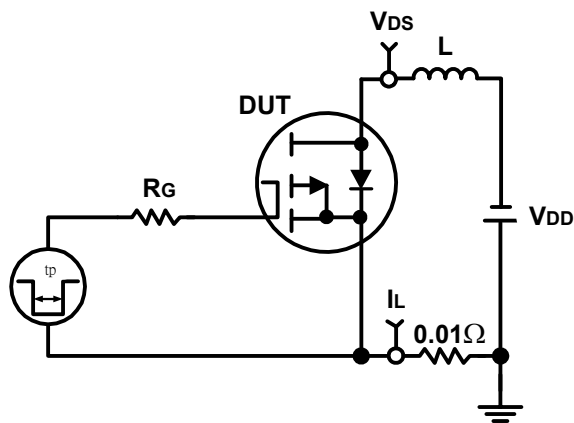
Drain-Source On Resistance



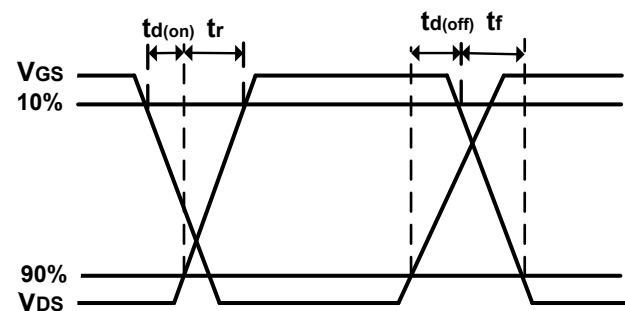
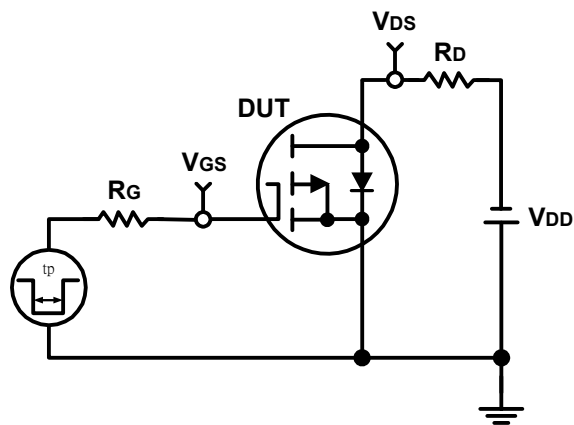
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


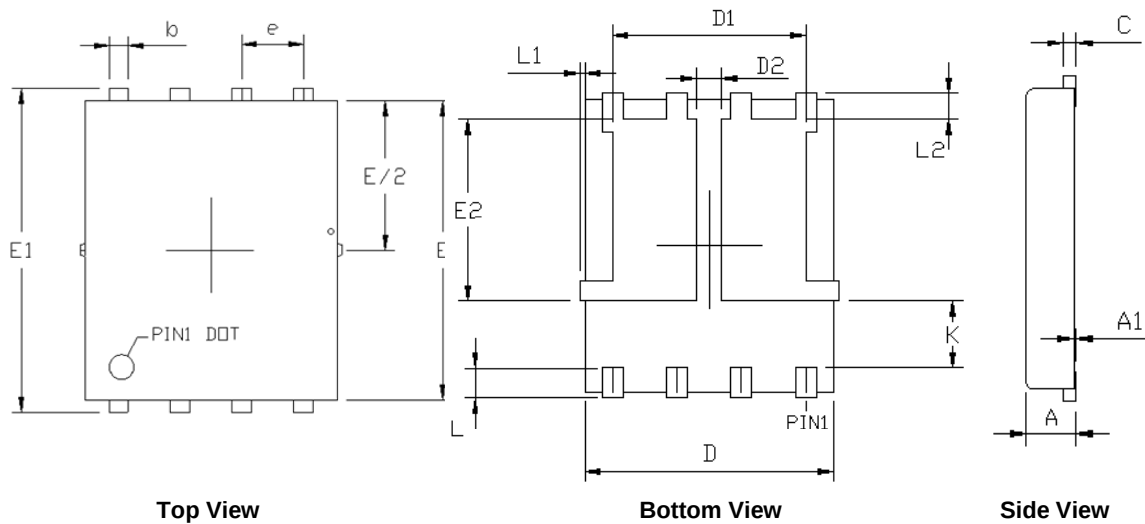
Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

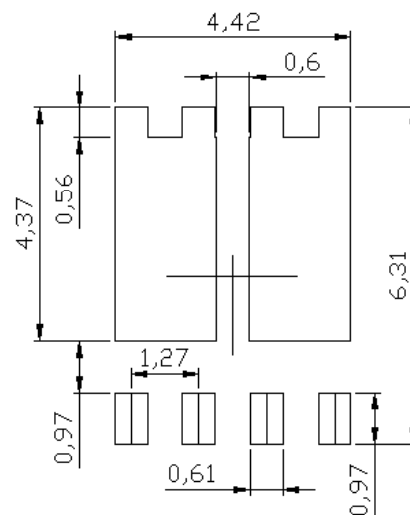


Package Information

DFN5x6C-8


SYMBOLS	DFN5x6C-8_EP2_P			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.900	1.200	0.035	0.047
A1	0.000	0.050	0.000	0.002
b	0.300	0.500	0.012	0.020
c	0.150	0.300	0.006	0.012
D	4.800	5.000	0.189	0.197
D1	3.550	4.550	0.140	0.179
D2	0.500	0.910	0.020	0.036
E	5.650	5.850	0.222	0.230
E1	5.900	6.200	0.232	0.244
E2	3.200	3.780	0.126	0.149
e	1.27 BSC		0.050 BSC	
K	1.100	-	0.043	-
L	0.500	0.800	0.020	0.031
L1	0.000	0.150	0.000	0.006
L2	0.325	0.610	0.013	0.024

RECOMMENDED LAND PATTERN



UNIT: mm